

* Assignments :- B.1.b (Using 90nm Foundry)

① B.1.b :-

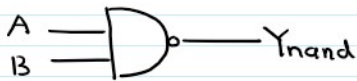
- a) 2 i/p NAND
- b) 2 i/p NOR
- c) 2 i/p AND
- d) 2 i/p OR

* 2 i/p NAND, 2 i/p NOR Gates:-

2 i/p NAND

2 i/p NOR

Symbols:



Expression:

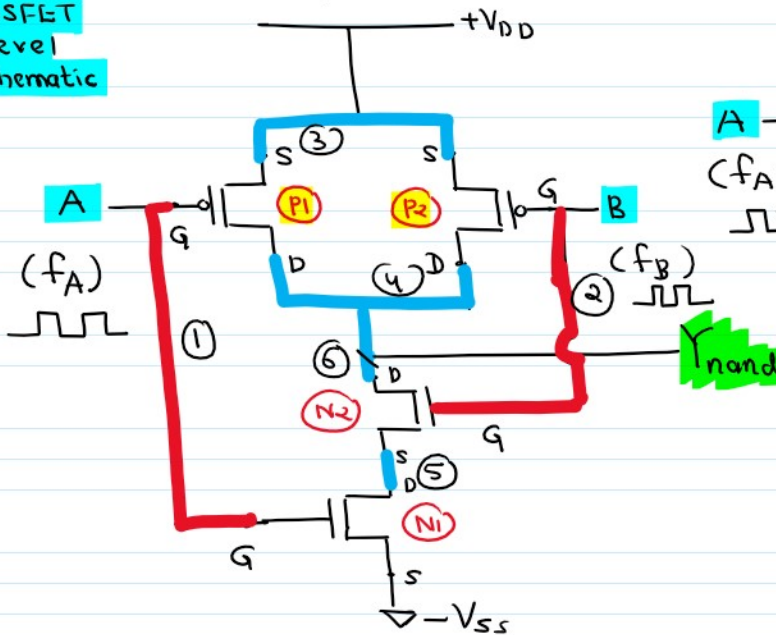
$$Y_{\text{nand}} = \overline{A \cdot B}$$

(P1//P2), (N1-N2)

$$Y_{\text{nor}} = \overline{A + B}$$

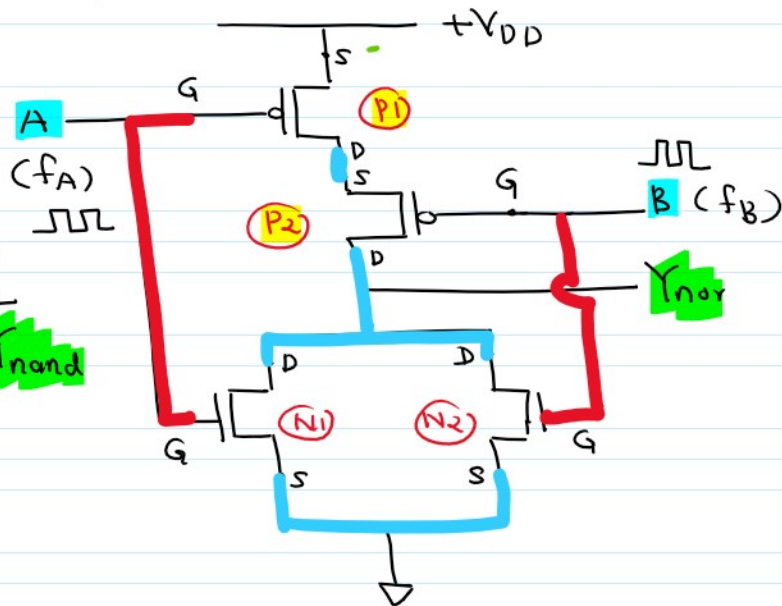
(P1-P2), (N1//N2)

MOSFET Level Schematic



$$f_A = \frac{1}{2} \cdot f_B$$

$T_A \quad T_B$



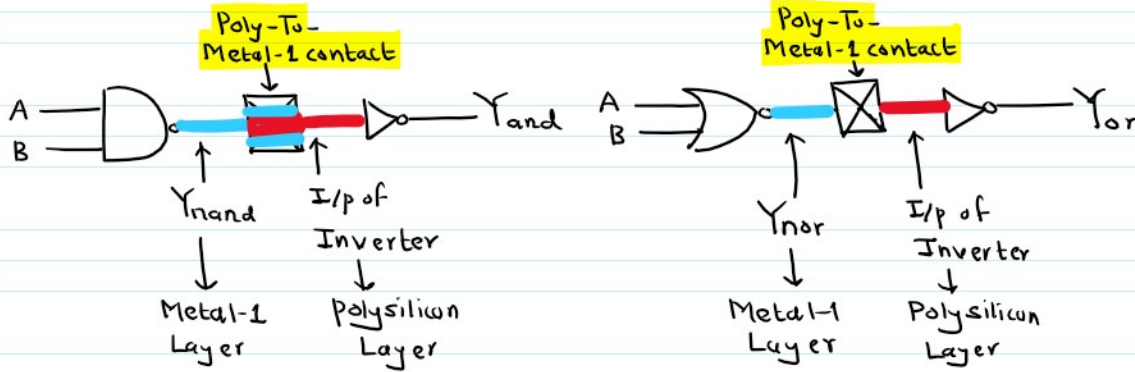
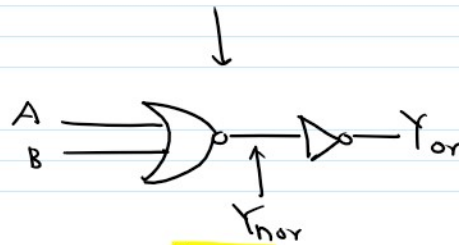
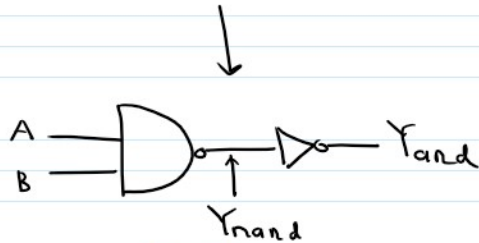
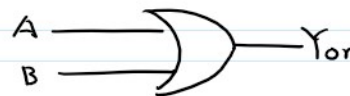
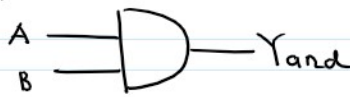
$$f_A = \frac{1}{2} f_B$$

T_A	T_B	
A	B	Y_{nand}
0	0	1
0	1	1
1	0	1
1	1	0

A	B	Y_{nor}
0	0	1
0	1	0
1	0	0
1	1	0

⊛ 2 i/p AND, 2 i/p OR Gate:-

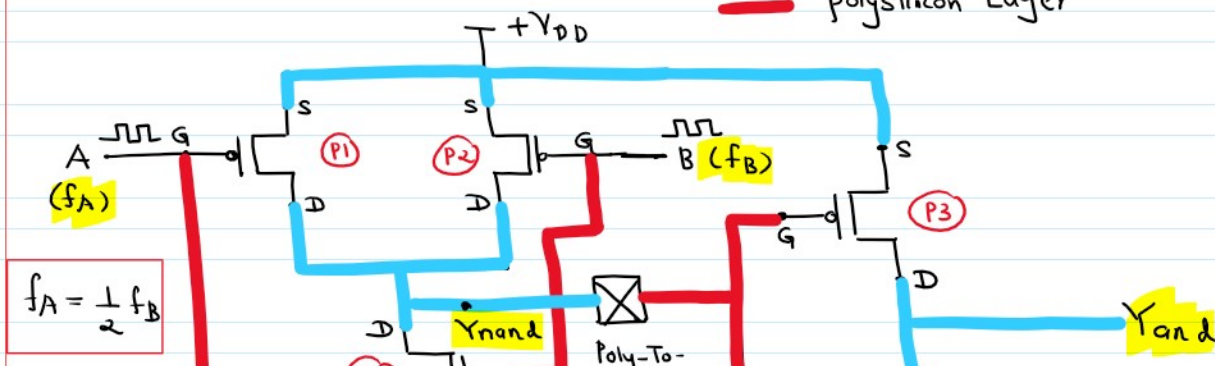
Symbols:-



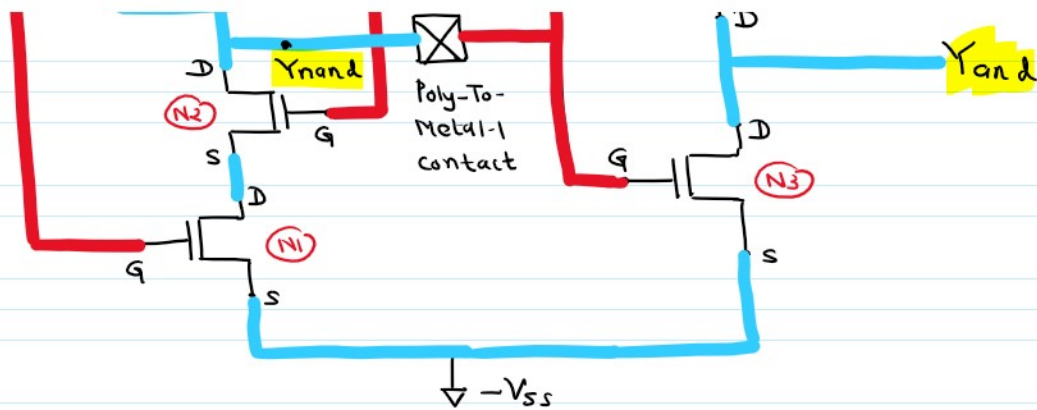
⊛ MOSFET-Level Schematics for 2 i/p AND, 2 i/p OR Gate:-

⊛ 2 i/p AND Gate :-

— Meta-1 Layer
— polysilicon Layer



$$f_A = \frac{1}{2} f_B$$



* 2 up OR Gate :-

